GP/2814

SONNENSCHEIN, NATH & ROSENTHAL
8000 Sears Tower
233 S. Wacker Drive
Chicago, IL 60606
312/876-0200

APPLICANTS:	Mitsuhiro Nakamura et al.	OLD DOCKET NO.:	P97,0322
		NEW DOCKET NO.:	09794353-0005
SERIAL NO.	08/809,463	GROUP ART UNIT:	2814
FILING DATE:	July 18, 1997	EXAMINER:	P. Cao

INVENTION: "MULTI-LAYERED STRUCTURE FOR FABRICATING AN OHMIC ELECTRODE AND OHMIC ELECTRODE"

AMENDMENT

Hon. Assistant Commissioner of Patents

Washington D.C. 2023

SIR:

Transmitted herewith is an amendment in the above-identified application.

_ Additional claim fee is required.

The fee has been calculated as shown below.

CLAIMS AS AMENDED						
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONAL FEE
TOTAL CLAIMS		MINUS	20	0	( ) X 9.00 ( ) X 18.00	0.00
INDEP. CLAIMS		MINUS	3	0	( ) X 39.00 () X 84.00	0.00
Application amended to contain any multiple dependent claims not previously paid for.				( ) YES (X) NO	( ) $135.00 ( ) $270.00 ONE TIME	
			TOTAL ADDITIONAL FEE FOR THIS AMENDMENT		$0.00	

X Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response to the Office Action dated May 8, 2002 for 2 months so that the period for response is extended to October 8, 2002.

X A check in the amount of $ 110.00 is attached to cover part of the extension of time fee. The Commissioner is hereby authorized to charge $ 290.00 to account No. 19-3140 for the remainder of the extension of time fee.

_ A check in the amount of $_____ is attached to cover the additional claim fee.

X The Commissioner is hereby authorized to charge any additional fees which may be required, or to credit any overpayment to account No. 19-3140. A duplicate of this sheet is enclosed.

When phoning re this application, please call 312/876-8000 - Ext. 2606.

SONNENSCHEIN NATH & ROSENTHAL

DATE: October 8, 2002

BY Christopher P. Rauch (Reg. No. 45,034)
Christopher P. Rauch

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited as first class mail in an envelope addressed to Asst. Commissioner of Patents, Washington, D.C. 20231 on October 8, 2002.

Christopher P. Rauch
Christopher P. Rauch

#32 C Andujar (2) M. Braunson 10/29/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Mitsuhiro Nakamura et al. OLD DOCKET NO.: P97,0322

NEW DOCKET NO.: 09794353-0005

SERIAL NO. 08/809,463 GROUP ART UNIT: 2814

FILING DATE: July 18, 1997 EXAMINER: P. Cao

INVENTION: "MULTI-LAYERED STRUCTURE FOR FABRICATING AN OHMIC ELECTRODE AND OHMIC ELECTRODE"

AMENDMENT

Hon. Assistant Commissioner for Patents
Washington, DC 20231

S I R:

This Amendment is filed in response to the Office Action of May 8, 2002. Please reconsider the application in view of the amendment and remarks presented below.

P1

IN THE CLAIMS

Please amend claims 1, 7, 9, 10, 17, and 19 as follows:

C1 1. (Three Times Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

C2 7. (Amended) The multi-layered structure for fabricating an ohmic electrode according to claim 4 wherein said metal film is one of a Ni film, a Co film, and an Al film.

C3 9. (Three Times Amended) A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.